

2SC535

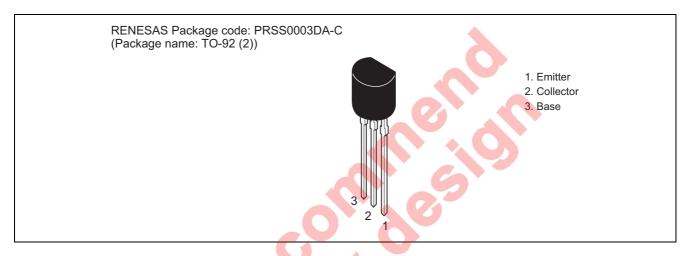
Silicon NPN Epitaxial Planar

REJ03G0683-0200 (Previous ADE-208-1047) Rev.2.00 Aug.10.2005

Application

VHF amplifier, mixer, local oscillator

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	30	V
Collector to emitter voltage	$V_{\sf CEO}$	20	V
Emitter to base voltage	V_{EBO}	4	V
Collector current	Ic	20	mA
Collector power dissipation	Pc	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

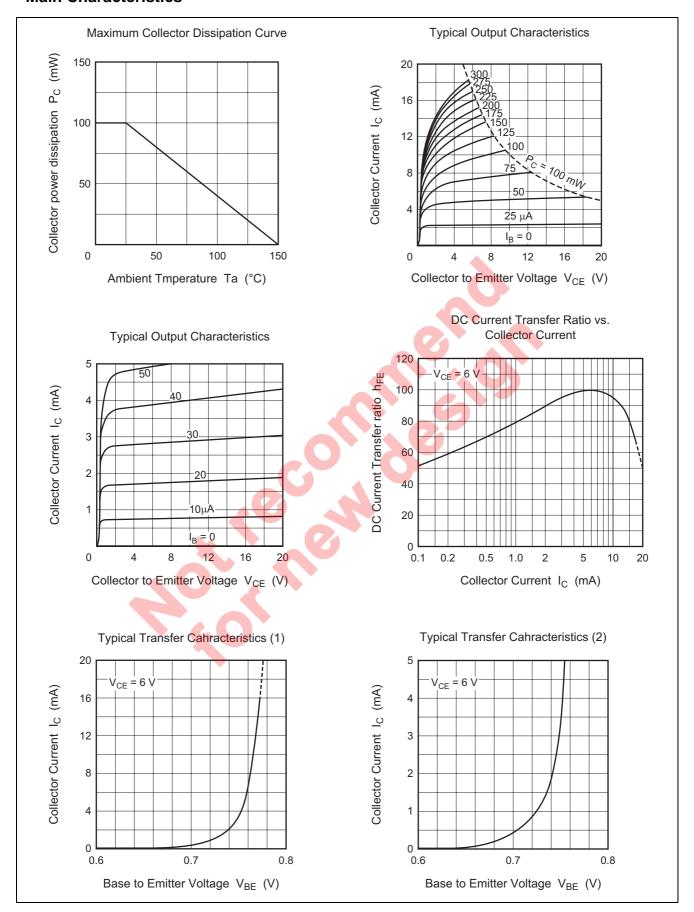
Electrical Characteristics

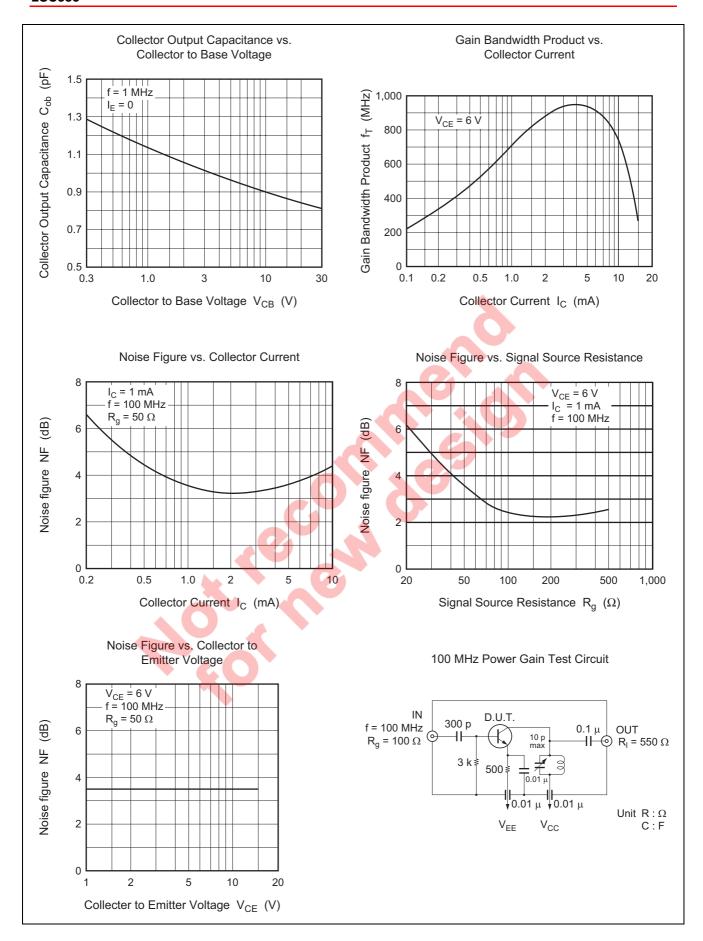
 $(Ta = 25^{\circ}C)$

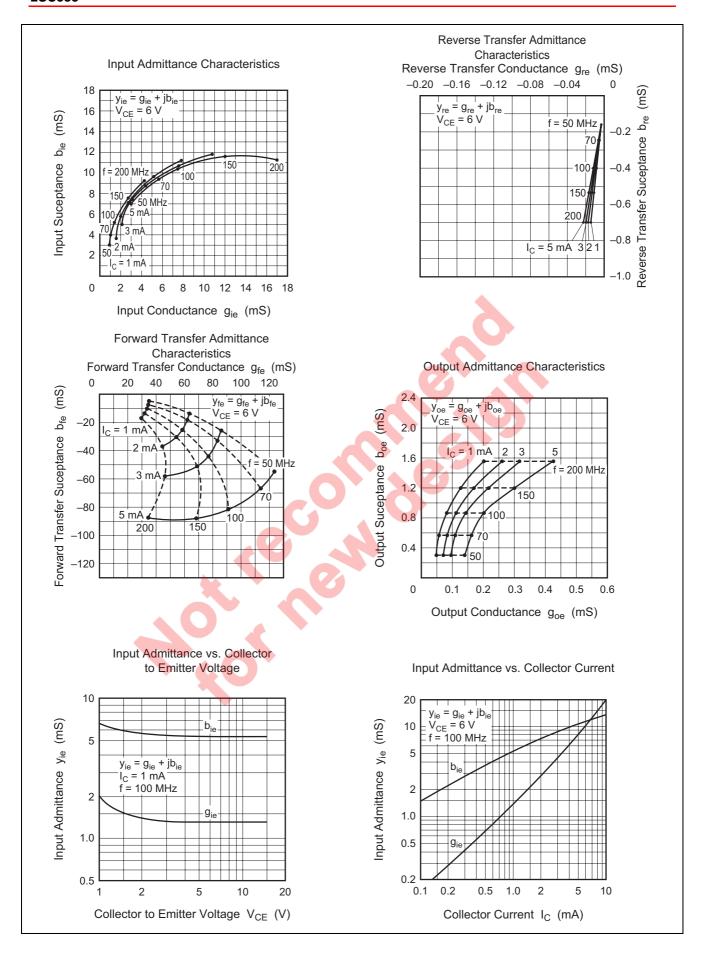
	Min	Тур	Max	Unit	Test conditions	
V _{(BR)CBO}	30	_	_	V	$I_C = 10 \mu\text{A}, I_E = 0$	
V _{(BR)CEO}	20	_	_	V	I _C = 1 mA, R _{BE} = ∞	
V _{(BR)EBO}	4	_	_	V	$I_E = 10 \mu A, I_C = 0$	
I _{CBO}	_	_	0.5	μΑ	V _{CB} = 10 V, I _E = 0	
h _{FE} *1	60	_	200		V _{CE} = 6 V, I _C = 1 mA	
V _{BE}	_	0.72	_	V	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA}$	
V _{CE(sat)}	_	0.17	_	V	$I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$	
f⊤	450	940	_	MHz	$V_{CE} = 6 \text{ V}, I_C = 5 \text{ mA}$	
Cob	_	0.9	1.2	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	
PG	17	20		dB	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA},$ f = 100 MHz	
NF	_	3.5	5.5	dB	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA},$ $f = 100 \text{ MHz}, R_{g} = 50 \Omega$	
yie		1.3 + j5.3		mS	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA},$ f = 100 MHz	
yre	-0	.078 – j0.	41	mS		
yfe		32 – j10		mS		
yoe	0	.08 + j0.8	2	mS		
_{FE} as follows	-			A		
B C 60 to 120 100 to 200						
	V(BR)CEO V(BR)EBO ICBO hFE*1 VBE VCE(sat) fT COb PG NF yie yre yfe yoe nFE as follows	V(BR)CEO 20 V(BR)EBO 4 ICBO — hFE*1 60 VBE — VCE(sat) — fT 450 Cob — PG 17 NF — yie yre yre — yfe yoe 0 0 nFE as follows.	V(BR)CEO 20 — V(BR)EBO 4 — ICBO — — hFE*1 60 — VBE — 0.72 VCE(sat) — 0.17 fT 450 940 Cob — 0.9 PG 17 20 NF — 3.5 yie 1.3 + j5.3 yre —0.078 – j0. yfe 32 – j10 yoe 0.08 + j0.8	V(BR)CEO 20 — — V(BR)EBO 4 — — ICBO — — 0.5 hFE* ¹ 60 — 200 VBE — 0.72 — VCE(sat) — 0.17 — fT 450 940 — Cob — 0.9 1.2 PG 17 20 — NF — 3.5 5.5 yie 1.3 + j5.3 — yre —0.078 – j0.41 — yfe 32 – j10 — yoe 0.08 + j0.82 —	V(BR)CEO 20 — — V V(BR)EBO 4 — — V ICBO — — 0.5 μA hFE** 60 — 200 VBE — 0.72 — V VCE(sat) — 0.17 — V fT 450 940 — MHz Cob — 0.9 1.2 pF PG 17 20 — dB NF — 3.5 5.5 dB yie 1.3 + j5.3 mS yre —0.078 – j0.41 mS yre 32 – j10 mS yre 0.08 + j0.82 mS nee as follows.	

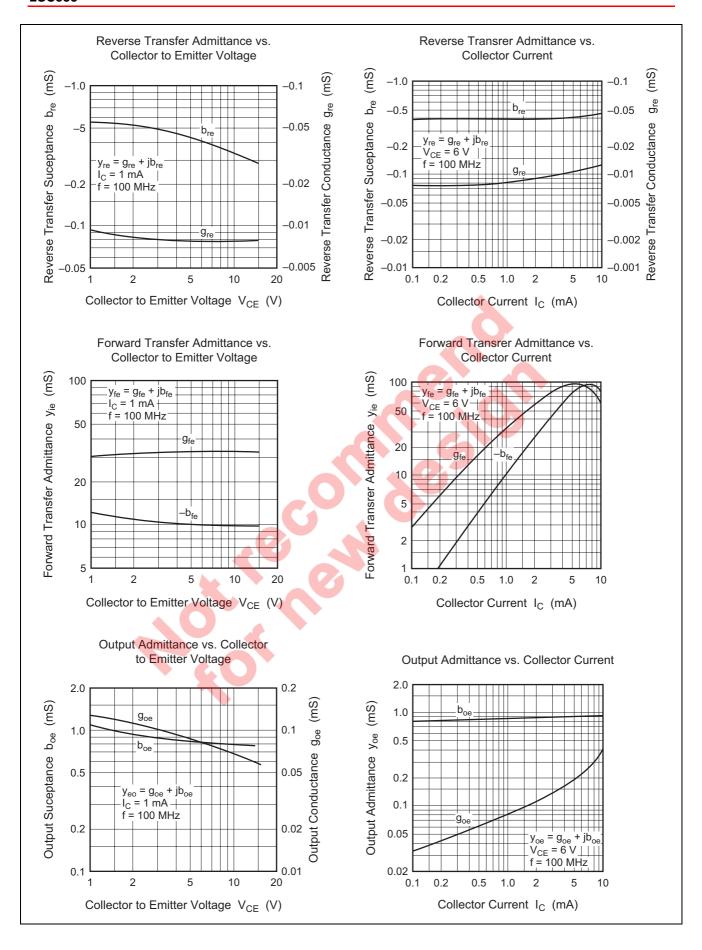
В	С	
60 to 120	100 to 200	

Main Characteristics

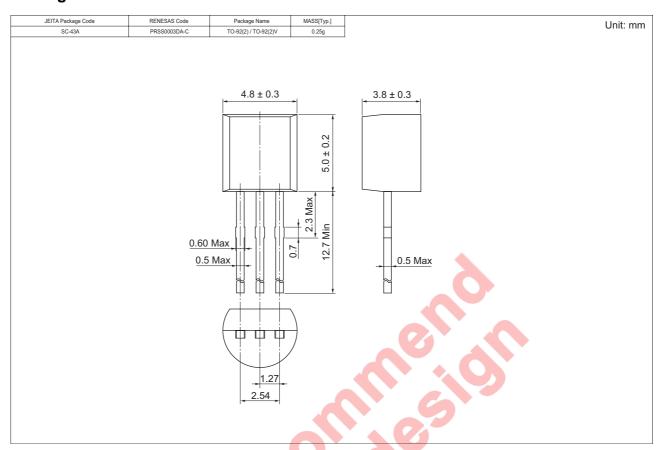








Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SC535BTZ	2500	Hold Box, Radial Taping
2SC535CTZ		

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